

Surface Mount Schottky Barrier Rectifier Voltage 50V Current 15Amperes

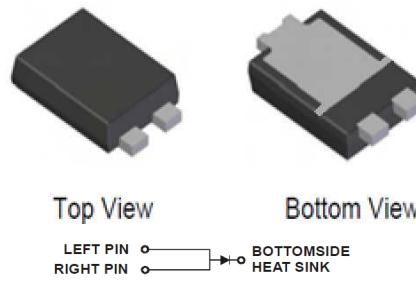
FEATURES

- Low Profile Design for Mobile Device
- Ideal for SMT Mounting
- Low forward voltage drop
- High forward surge capability
- Excellent High Temperature Stability

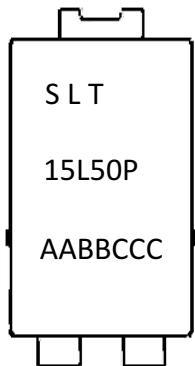
MECHANICAL DATA

- Epoxy : UL94 V-0 rated flame retardant
- Case: TO-277
- Terminals: Lead solderable
- Weight: Approximated 0.129grams

Primary Characteristic	
I _O	20A
V _{RRM}	50V
I _{FSM}	275A
V _F (IF=5.0A), T _A =125°C	0.29V
T _{Jmax}	125°C



Marking Information



SL T = Product Type Marking Code

15L50PU= Part Number Marking Code

AABBCCC =Product Tracking Code

Maximum Ratings Ta=25°C unless otherwise specified			
Characteristics	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	V
Working Peak Reverse Voltage	V _{RWM}	50	V
Maximum DC Blocking Voltage	V _{DC}	50	V
RMS Reverse Voltage	V _{RMS}	35	V
Maximum Average ForwardRectified Current	I _O	15	A
Peak Forward Surge Current,8.3 msSingle Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	275	A
Operating Temperature Range - in DC Forward Mode	T _J	-65 to +125	°C
	T _{Jmax}	125	°C
Storage Temperature Range	T _{STG}	-65 to +150	°C

Notes:(1) Pulse test: 300 µs pulse width, 1 % duty cycle

Electrical Characteristics (Ta=25°C unless otherwise specified)				
Characteristics	Symbol	Value	Unit	
Forward Voltage I _F =5.0A, T _A =25°C I _F =15.0A, T _A =25°C I _F =5.0A, T _A =125°C I _F =15.0A, T _A =125°C	V _F	Typ. 0.39 0.49 0.29 0.39	Max. 0.44 0.53 0.34 0.46	V
		-	-	V
		-	-	V
		-	-	V
		-	-	V
Maximum Reverse Current at Rated V _{RRM} VR=50V, T _A =25°C VR=50V, T _A =125°C	I _R	Typ. -	Max. 200 10	μA
		-	25	mA
		-	-	-
Thermal Characteristics				
Characteristics	Symbol	Value	Unit	
Typical thermal resistance, junction to ambient	R _{θJA}	70	°C /W	
Typical thermal resistance, junction to terminal	R _{θJT}	5	°C /W	

Notes:(2) Device mounted on FR-4 substrate, 2oz copper, with minimum recommended pad layout.

Notes:(3) Short duration pulse test used to minimize self-heating effect.

Notes:(4) Device might risk thermal failure during applied reverse bias, while typical T_c > 105°C is measured from die straight up to top center of the casesurface.

Characteristics Curves

Fig.1 Typical Instantaneous Forward Characteristics

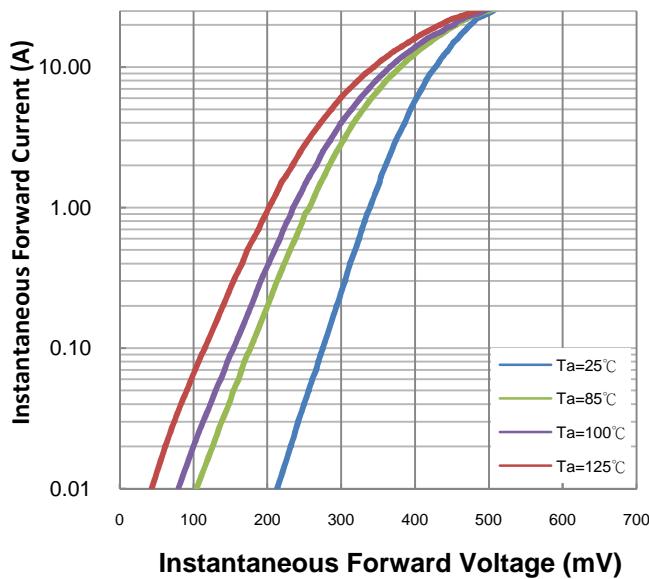


Fig.2 Typical Reverse Characteristics

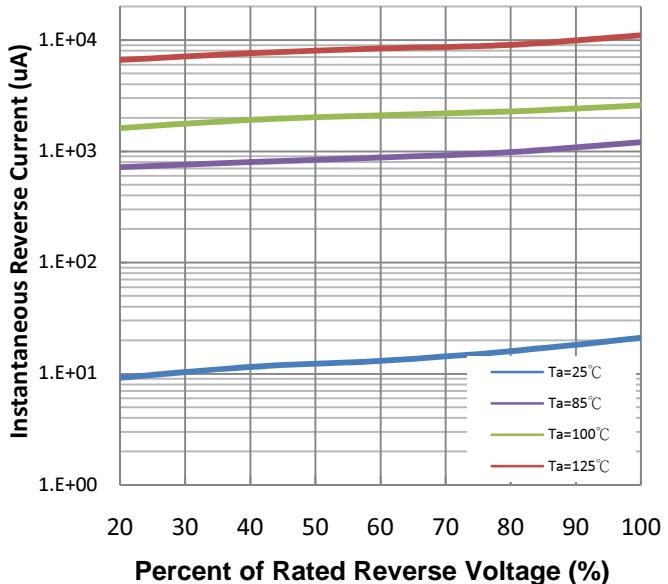


Fig.3 Typical Forward Current Derating Curve

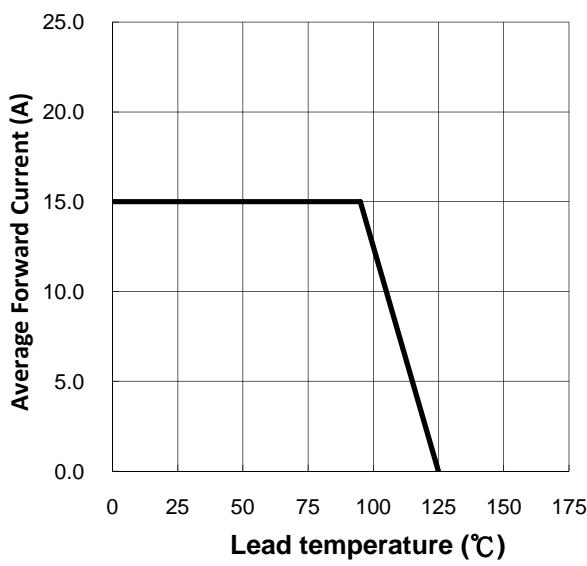
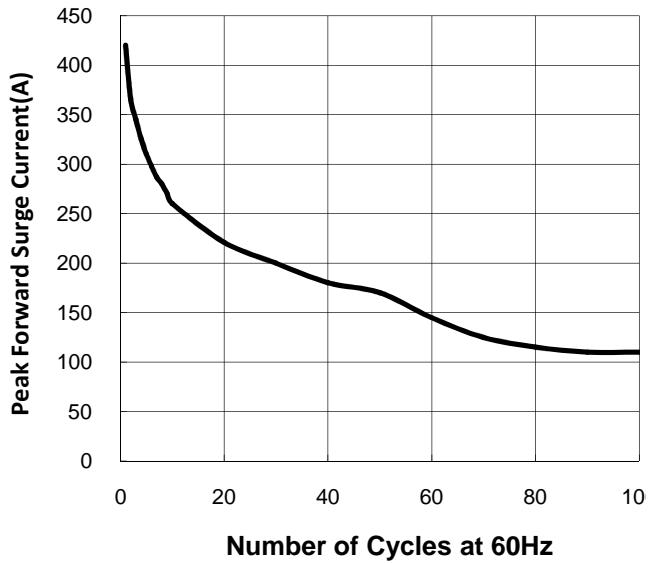
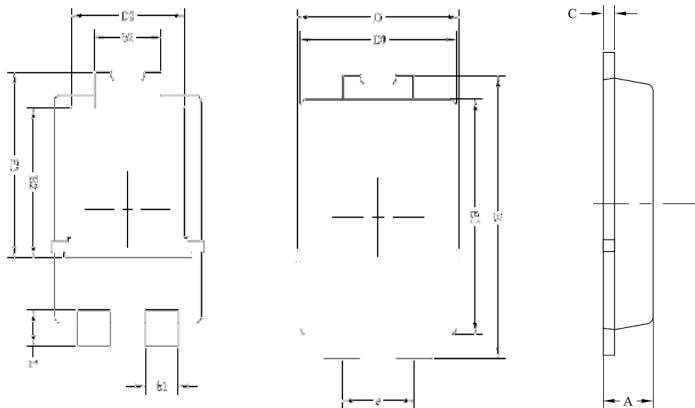


Fig.4 Max. Non-repetitive Forward Surge Current



Package Outline Dimensions



	MIN	NOM	M/ %
A	1.05	1.10	1.0
b1	0.80	0.90	0.9
b2	1.70	1.79	1.8
b3	0.15	0.25	0.2
C	0.20	0.25	0.2
D	4.00	4.20	4.1
D1	3.90	3.98	4.0
D2	2.95	3.05	3.0
E	6.40	6.50	6.0
E1	5.30	5.40	5.4
E2	3.45	3.55	3.6
E3	4.20	4.40	4.0
e		1.84 Typ	
L	0.75	0.85	0.8

Unit: mm

